IN THE SPECIFICATION

Page 8, line 8

Page 8, line 9:

The apparatus 10 includes an enclosure 20 which may be formed in part by an electrode 22, and electrode 24 displaced from, but preferably substantially parallel to, the electrode 22 and magnets 26 and 28 disposed in a transverse (preferably substantially perpendicular) relationship to the electrodes 22 and 24. The electrode 22 is disposed in a B1 contiguous but spaced and substantially parallel relationship to the wafer 16 and is movable in position toward or away from the wafer, as indicated by a double-headed arrow 25. The spacing between the wafer 16 and the electrode 22 may illustratively be in the order of 0.1 – 2mm. A plate 30 extending from the magnet 28 in a substantially parallel and adjacent, but spaced, relationship to the electrode 22 also defines the enclosure 20. A ring 32 extending from the magnet 26 to a position spaced from, but adjacent to, the electrode 24 also defines in part the enclosure 20. The plate 30 and the ring 32 may be considered as electrical conductors.

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As will be seen, the combination of the electrode 22 and the wafer 16 in Figure 5a is seen as a single electrode or plate in a capacitor 50 in Figure 5b. The other electrode or plate in the capacitor 50 is defined by the positive ions in the enclosure 20 at positions B2 adjacent the electrode 24. These positive ions are schematically illustrated by dots (.) at 51 in Figure 3. The dielectric between the plates of the capacitor 50 may be considered to be the insulating layer 14. The impedance of the capacitor 50 is accordingly relatively

low because the insulating layer 14 is relatively thin and because the dielectric constant of the insulating layer is lower than the dielectric constant of air or the dielectric constant of a vacuum.